

**CMPDM7003**  
**SURFACE MOUNT**  
**N-CHANNEL**  
**ENHANCEMENT-MODE**  
**SILICON MOSFET**



[www.centrasemi.com](http://www.centrasemi.com)



**SOT-23 CASE**

**DESCRIPTION:**

The CENTRAL SEMICONDUCTOR CMPDM7003 is an Enhancement-mode N-Channel Field Effect Transistor, manufactured by the N-Channel DMOS Process, designed for high speed pulsed amplifier and driver applications. This MOSFET offers low  $r_{DS(ON)}$  and ESD protection up to 2kV.

**MARKING CODE: C7003**

**FEATURES:**

- ESD protection up to 2kV
- Low  $r_{DS(ON)}$
- Low  $V_{DS(ON)}$
- Low threshold voltage
- Fast switching
- Logic level compatibility

**APPLICATIONS:**

- Load/Power switches
- Power supply converter circuits
- Battery powered portable equipment

**MAXIMUM RATINGS:** ( $T_A=25^\circ\text{C}$ )

Drain-Source Voltage
Drain-Gate Voltage
Gate-Source Voltage
Continuous Drain Current
Maximum Pulsed Drain Current
Power Dissipation
Operating and Storage Junction Temperature
Thermal Resistance

**SYMBOL**

$V_{DS}$	50
$V_{DG}$	50
$V_{GS}$	12
$I_D$	280
$I_{DM}$	1.5
$P_D$	350
$T_J, T_{stg}$	-65 to +150
$\Theta_{JA}$	357

**UNITS**

V
V
V
mA
A
mW
$^\circ\text{C}$
$^\circ\text{C/W}$

**ELECTRICAL CHARACTERISTICS:** ( $T_A=25^\circ\text{C}$  unless otherwise noted)

SYMBOL	TEST CONDITIONS	MIN	TYP	MAX	UNITS
$I_{GSSF}, I_{GSSR}$	$V_{GS}=5.0\text{V}$			100	nA
$I_{GSSF}, I_{GSSR}$	$V_{GS}=10\text{V}$			2.0	$\mu\text{A}$
$I_{GSSF}, I_{GSSR}$	$V_{GS}=12\text{V}$			2.0	$\mu\text{A}$
$I_{DSS}$	$V_{DS}=50\text{V}, V_{GS}=0$			50	nA
$BV_{DSS}$	$V_{GS}=0, I_D=10\mu\text{A}$	50			V
$V_{GS(th)}$	$V_{DS}=V_{GS}, I_D=250\mu\text{A}$	0.49		1.0	V
$V_{SD}$	$V_{GS}=0, I_S=115\text{mA}$			1.4	V
$r_{DS(ON)}$	$V_{GS}=1.8\text{V}, I_D=50\text{mA}$		1.6	3.0	$\Omega$
$r_{DS(ON)}$	$V_{GS}=2.5\text{V}, I_D=50\text{mA}$		1.3	2.5	$\Omega$
$r_{DS(ON)}$	$V_{GS}=5.0\text{V}, I_D=50\text{mA}$		1.1	2.0	$\Omega$
gFS	$V_{DS}=10\text{V}, I_D=200\text{mA}$	200			mS
$C_{rss}$	$V_{DS}=25\text{V}, V_{GS}=0, f=1.0\text{MHz}$			5.0	pF
$C_{iss}$	$V_{DS}=25\text{V}, V_{GS}=0, f=1.0\text{MHz}$			50	pF
$C_{oss}$	$V_{DS}=25\text{V}, V_{GS}=0, f=1.0\text{MHz}$			25	pF

R1 (27-January 2010)

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**SOT-23 CASE - MECHANICAL OUTLINE**



**LEAD CODE:**

- 1) Gate
- 2) Source
- 3) Drain

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<b>DIMENSIONS</b>				
SYMBOL	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	0.003	0.007	0.08	0.18
B	0.006	-	0.15	-
C	-	0.005	-	0.13
D	0.035	0.043	0.89	1.09
E	0.110	0.120	2.80	3.05
F	0.075		1.90	
G	0.037		0.95	
H	0.047	0.055	1.19	1.40
I	0.083	0.098	2.10	2.49
J	0.014	0.020	0.35	0.50

SOT-23 (REV: R3)

R1 (27-January 2010)